## NSN 5961-01-023-8045

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View Online at https://aerobasegroup.com/nsn/5961-01-023-8045 **Inclosure Material:** Metal **Overall Length:** 1.573 inches **Overall Height:** Between 0.250 inches and 0.450 inches **Overall Width:** 1.050 inches **Mounting Facility Quantity:** Joint Electronic Device Engineering Council/jedec/case Outline Designation: To-3 **Electrode Internally-electrically Connected To Case:** Anode **Mounting Method:** Unthreaded hole **Semiconductor Material:** Silicon Voltage Rating In Volts Per Characteristic: 100.0 reverse voltage, peak **Current Rating Per Characteristic:** 20.00 amperes source cutoff current preset **Power Rating Per Characteristic:** 5.0 watts small-signal input power, common-collector outside diameter and 0.5 watts small-signal input power, common-collector peak **Maximum Operating Tempurature Per Measurement Point:** 100.0 degrees celsius junction **Special Features:** Lead diameter 0.057 in. Max. **Test Data Document:** 10001-2874059 drawing (this is the basic governing drawing, such as a contractor drawing, original equipment manufacturer drawing, etc.; excludes any specification, standard or other document that may be referenced in a basic governing drawing) **Terminal Type And Quantity:** 2 pin and 1 case Shelf Life: N/a **Unit Of Measure: Demilitarization:**